

# RF Power MOSFET Transistor 5 W, 2 - 175 MHz, 28 V

Rev. V1

#### **Features**

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- · High saturated output power
- · Lower noise figure than bipolar devices
- RoHS Compliant

#### **ABSOLUTE MAXIMUM RATINGS AT 25° C**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V <sub>DS</sub>	65	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	I <sub>DS</sub>	1.4	Α
Power Dissipation	P <sub>D</sub>	15.8	W
Junction Temperature	TJ	200	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Thermal Resistance	θ <sub>JC</sub>	11.1	°C/W

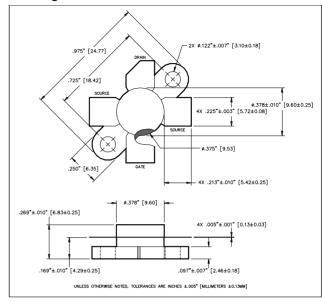
#### **TYPICAL DEVICE IMPEDANCE**

F (MHz)	Z <sub>IN</sub> (Ω)	Z <sub>LOAD</sub> (Ω)		
100	15 - j121.0	57.0 + j23.0		
150	39.0 - j77.0	55.0 +j23.0		
175	41.0 - j38.0	56.0 + j19.0		
200	34.0—j14.0 56.0 + j20.0			
$V_{DD}$ = 28V, $I_{DQ}$ = 50mA, $P_{OUT}$ = 5W				

 $Z_{\text{IN}}$  is the series equivalent input impedance of the device from gate to source.

Z<sub>LOAD</sub> is the optimum series equivalent load impedance as measured from drain to ground.

#### **Package Outline**



LETTER	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	24.64	24.89	.970	.980
В	18.29	18.54	.720	.730
С	20.07	20.83	.790	.820
D	9.47	9.73	.373	.383
E	6.22	6.48	.245	.255
F	5.64	5.79	.222	.228
G	2.92	3.30	.115	.130
Н	2.29	2.67	.090	.105
J	4.04	4.55	.159	.179
К	6.58	7.39	.259	.291
L	.10	.15	.004	.006

#### **ELECTRICAL CHARACTERISTICS AT 25°C**

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	-	V	V <sub>GS</sub> = 0.0 V , I <sub>DS</sub> = 20.0 mA
Drain-Source Leakage Current	I <sub>DSS</sub>	-	1.0	mA	V <sub>GS</sub> = 28.0 V , V <sub>GS</sub> = 0.0 V
Gate-Source Leakage Current	I <sub>GSS</sub>	-	1.0	μA	V <sub>GS</sub> = 20.0 V , V <sub>DS</sub> = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V <sub>DS</sub> = 10.0 V , I <sub>DS</sub> = 10 mA
Forward Transconductance	$G_{M}$	80	-	S	$V_{DS}$ = 10.0 V , $I_{DS}$ = 10 mA , $\Delta$ $V_{GS}$ = 1.0 V, 80 $\mu$ s Pulse
Input Capacitance	C <sub>ISS</sub>	-	7	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	5	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C <sub>RSS</sub>	-	2.4	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Power Gain	G <sub>P</sub>	11	-	dB	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 50 mA, P <sub>OUT</sub> = 5.0 W F =175 MHz
Drain Efficiency	ŋ <sub>D</sub>	55	-	%	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 50 mA, P <sub>OUT</sub> = 5.0 W F =175 MHz
Load Mismatch	VSWR-T	-	20:1	-	$V_{DD}$ = 28.0 V, $I_{DQ}$ = 50 mA, $P_{OUT}$ = 5.0 W F =175 MHz

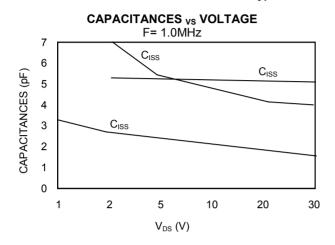
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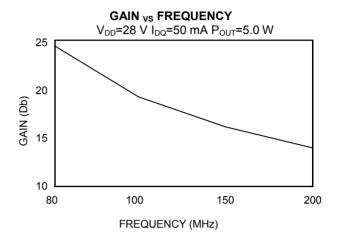


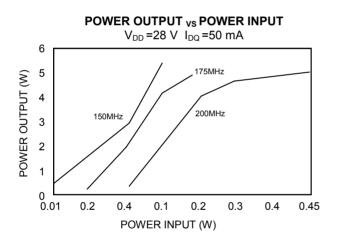
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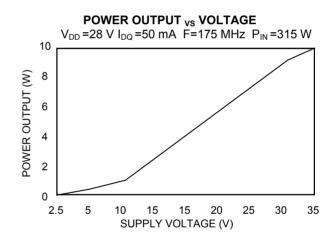
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#### **Typical Broadband Performance Curves**







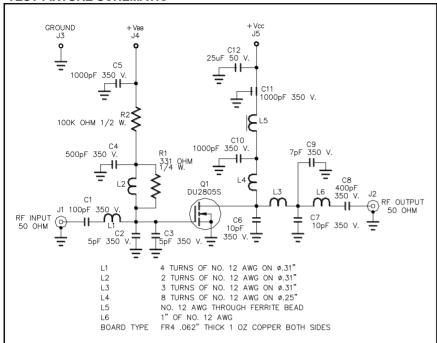




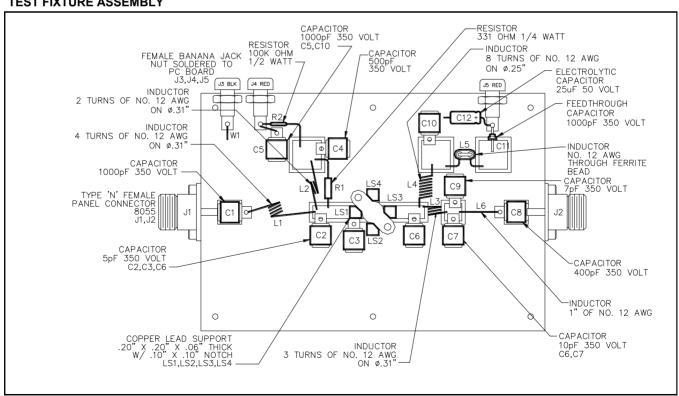
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#### **TEST FIXTURE ASSEMBLY**



## **DU2805S**



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